

Features :

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications :

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

| V _{DSM} ,V _{RSM} | V _{DRM} ,V _{RRM} | 品名 |
|------------------------------------|------------------------------------|-----------|
| 2700V | 2600V | Mx110T260 |
| 2900V | 2800V | Mx110T280 |
| 3100V | 3000V | Mx110T300 |
| 3300V | 3200V | Mx110T320 |
| 3500V | 3400V | Mx110T340 |
| 3700V | 3600V | Mx110T360 |

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | T _j (°C) | VALUE | | | UNIT |
|--------------------------------------|--|--|---------------------|-------|------|------|----------------------------------|
| | | | | Min | Type | Max | |
| I _{T(AV)} | Mean on-state current | 180° half sine wave 50Hz Single side cooled, T _C =85°C | 125 | | | 110 | A |
| I _{T(RMS)} | RMS on-state current | | | | | 173 | A |
| I _{DRM} I _{RRM} | Repetitive peak current | at V _{DRM} at V _{RRM} | 125 | | | 20 | mA |
| I _{TSM} | Surge on-state current | V _R =60%V _{RRM} , t=10ms half sine | 125 | | | 2.1 | kA |
| I ² t | I ² t for fusing coordination | | 125 | | | 22 | 10 ³ A ² s |
| V _{TO} | Threshold voltage | | 125 | | | 1.15 | V |
| r _T | On-state slope resistance | | | | | 2.88 | mΩ |
| V _{TM} | Peak on-state voltage | I _{TM} =330A | 25 | | | 2.80 | V |
| dv/dt | Critical rate of rise of off-state voltage | V _{DM} =67%V _{DRM} | 125 | | | 1000 | V/μs |
| di/dt | Critical rate of rise of on-state current | Gate source 1.5A t _r ≤ 0.5μs Repetitive | 125 | | | 200 | A/μs |
| I _{GT} | Gate trigger current | V _A =12V, I _A =1A | 25 | 30 | | 150 | mA |
| V _{GT} | Gate trigger voltage | | | 0.8 | | 2.5 | V |
| I _H | Holding current | | | 10 | | 200 | mA |
| I _L | Latching current | | | | | 1000 | mA |
| V _{GD} | Non-trigger gate voltage | V _{DM} =67%V _{DRM} | 125 | | | 0.20 | V |
| R _{th(j-c)} | Thermal resistance Junction to case | D.C. Single side cooled per chip | | | | 0.19 | °C/W |
| R _{th(c-h)} | Thermal resistance case to heatsink | D.C. Single side cooled per chip | | | | 0.15 | °C/W |
| V _{iso} | Isolation voltage | 50Hz,R.M.S,t=1min,I _{iso} :1mA(MAX) | | 4000 | | | V |
| F _m | Terminal connection torque(M6) | | | 4.5 | | 6 | N·m |
| | Mounting torque(M6) | | | 4.5 | | 6 | N·m |
| T _{vj} | Junction temperature | | | -40 | | 125 | °C |
| T _{stg} | Stored temperature | | | -40 | | 125 | °C |
| W _t | Weight | | | | 320 | | g |
| Outline | M02 | | | | | | |

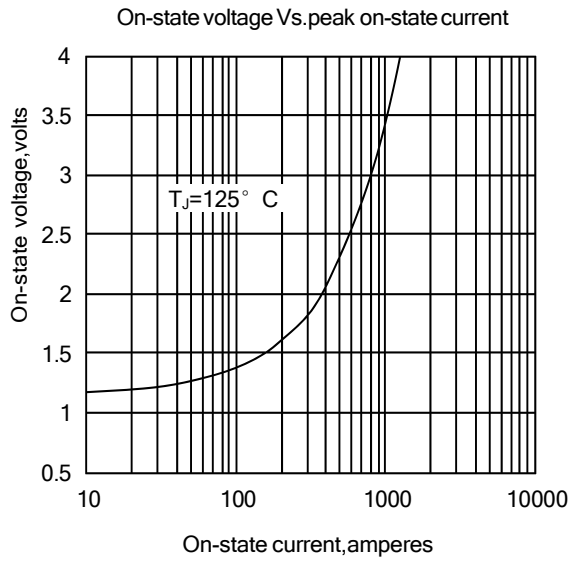


Fig. 1

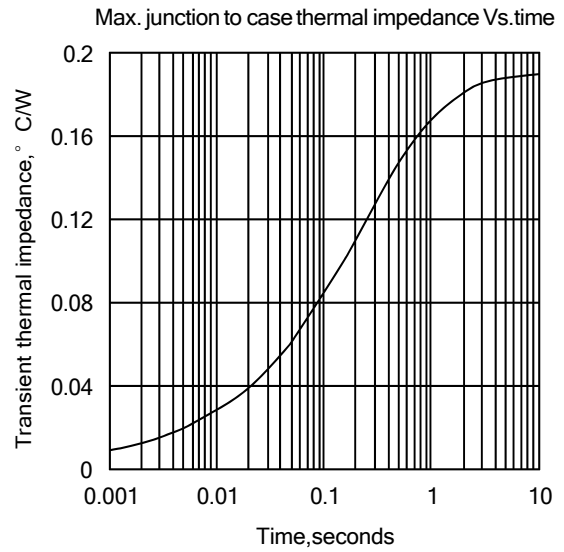


Fig. 2

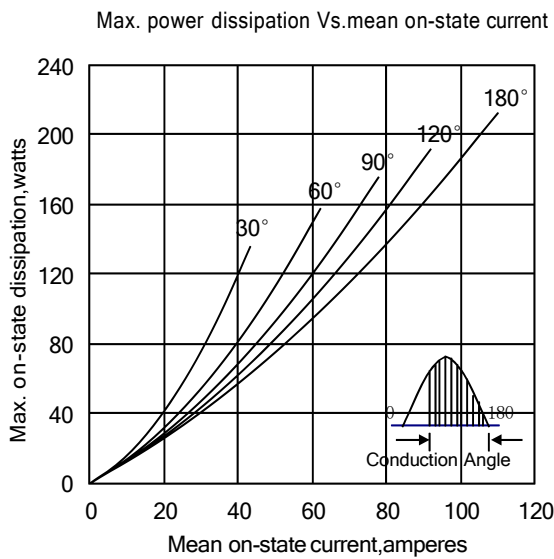


Fig. 3

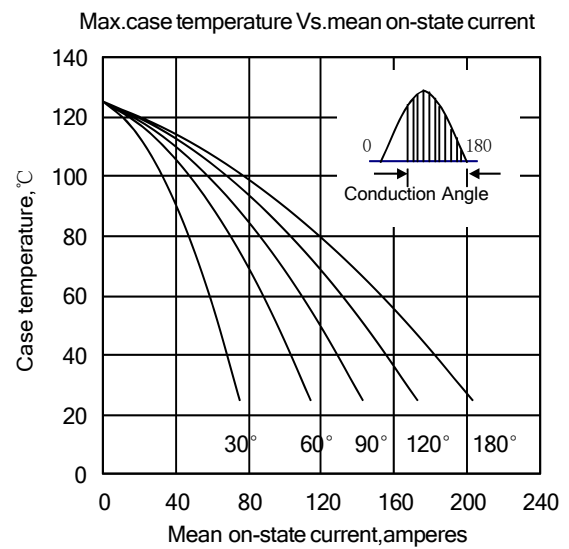


Fig. 4

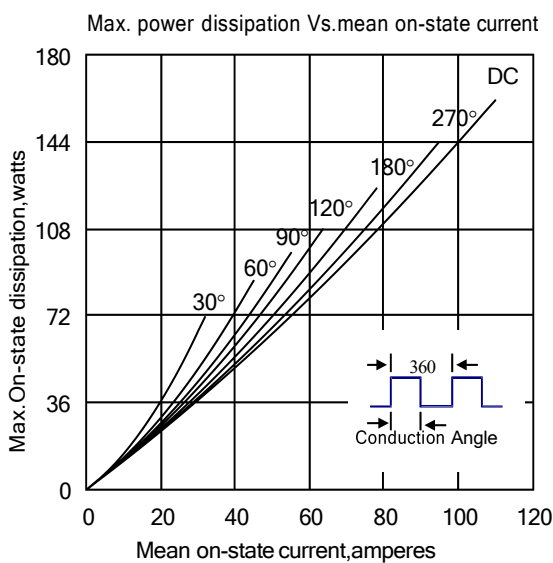


Fig. 5

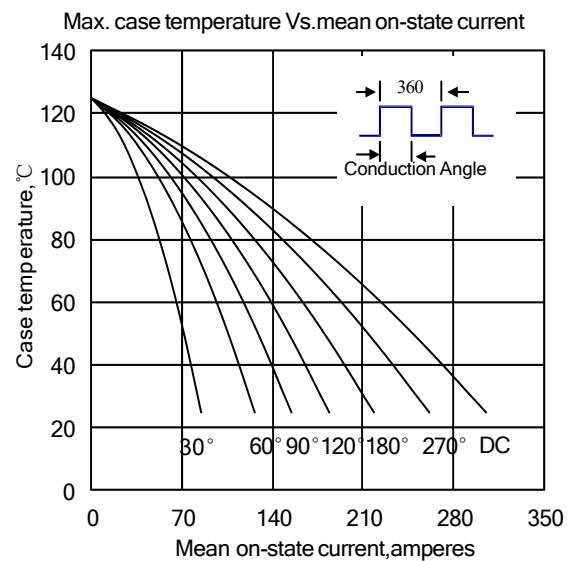


Fig. 6

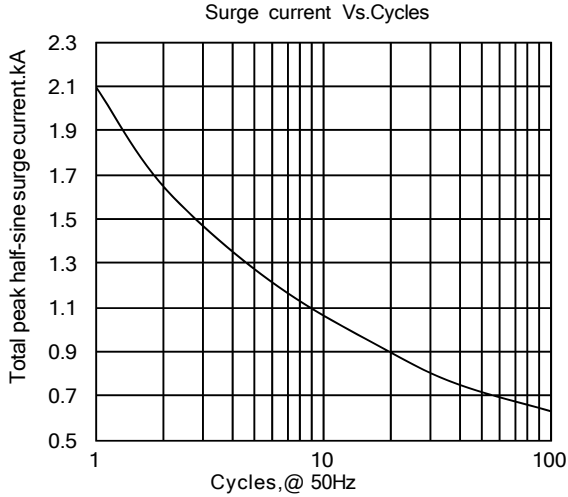


Fig. 7

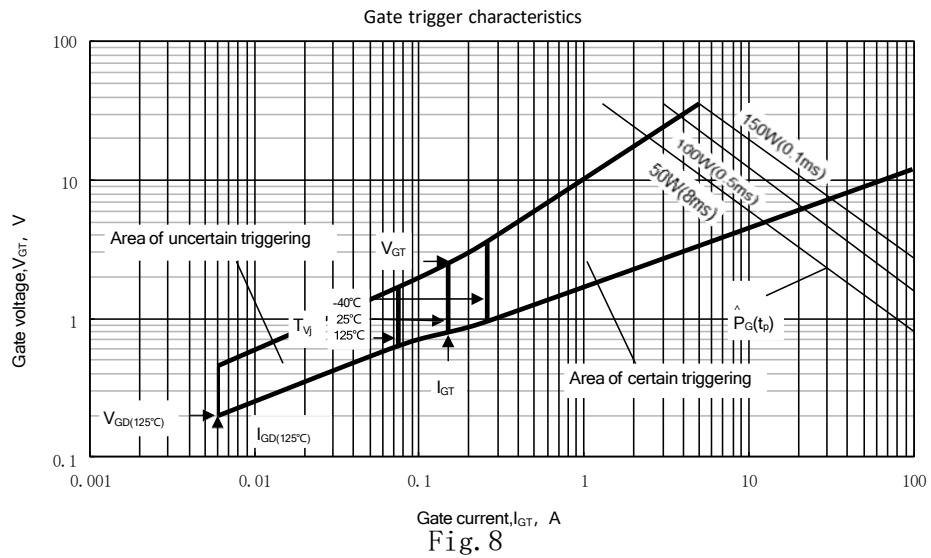
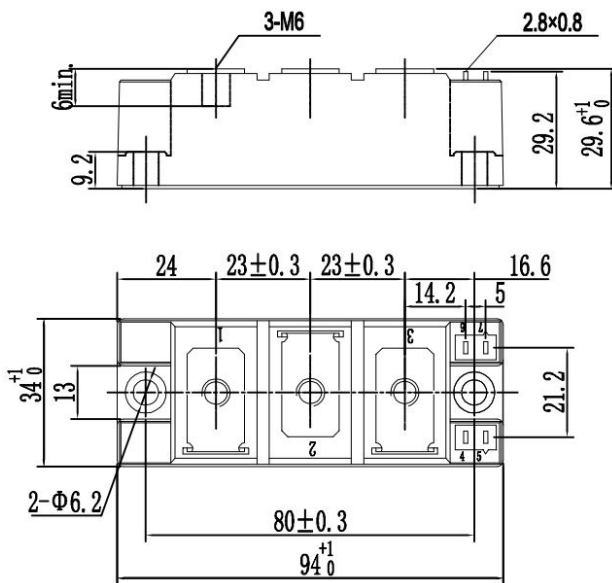


Fig. 8

Outline:



Unmarked dimensional tolerance: ±0.5mm

